

AMENDMENTS TO THE SPECIFICATION**IN THE TITLE:**

Please amend the title as follows:

A1

**METHOD FOR PRODUCING A FLAT INTERFACE MULTILAYER DEPOSITION
PROCESS INCLUDING FORMATION OF A SILICIDE FOR A METAL-SILICON
CONTACT BARRIER FILM**

IN THE ABSTRACT:

Please amend the abstract as follows:

A2

A method for forming a conductive contact ~~having an atomically flat surface on a~~ semiconductor substrate. A first layer containing titanium, a second layer containing titanium and an element (one of cobalt, tungsten, titanium, or molybdenum), and a third layer containing titanium ~~are is~~ deposited on ~~a silicon the~~ substrate and the resulting structure is annealed in a nitrogen-containing atmosphere at about 500 °C to about 700 °C. ~~A flat interface is formed that prevents diffusion of conductive materials into the underlying silicon substrate. The~~ annealing forms a first silicide layer including the element in contact with the substrate and a second silicide layer including titanium and the element overlying the first silicide layer. The method can be used to form contacts for very small devices and shallow junctions, such as are required for ULSI shallow junctions.